

Small Signal Transistor

FMMT2484

■ Features

- 60 Volt V_{CE0} .

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	6	V
Peak collector current	I_{CM}	200	mA
Collector current	I_C	50	mA
Power dissipation	P_{tot}	330	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cutoff current	I_{CBO}	$V_{CB}=45\text{V}, I_E=0$			10	nA
		$V_{CB}=45\text{V}, T_{amb}=150^\circ\text{C}$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			10	nA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C=1\text{A}, I_B=100\mu\text{A}$			0.35	V
Base-emitter voltage *	V_{BE}	$I_C=1\text{A}, V_{CE}=5\text{V}$			0.95	V
DC current gain *	h_{FE}	$I_C=10\mu\text{A}, V_{CE}=5\text{V}$	100		500	
Output capacitance	C_{obo}	$V_{CB}=5\text{V}, f=140\text{KHz}$			6	pF
Input capacitance	C_{ibo}	$V_{BE}=0.5\text{V}, f=140\text{KHz}$			6	pF
Output capacitance	NF	$I_C=200\mu\text{A}, V_{CE}=5\text{V}, R_g=2\text{k}\Omega$ $f=1\text{kHz}, f=200\text{Hz}$			3	dB
		$I_C=200\mu\text{A}, V_{CE}=5\text{V}, R_g=2\text{k}\Omega$ $f=30\text{Hz to } 15\text{kHz at } -3\text{dB points}$			3	dB

* Pulse test: $t_p \leq 300\mu\text{s}; d \leq 0.02$.

■ Marking

Marking	4G
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